

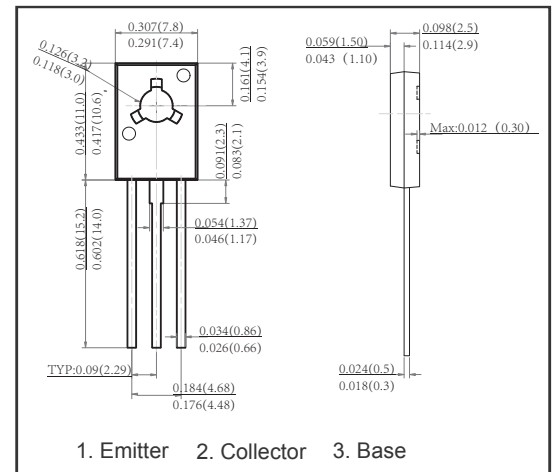
## TO-126 Plastic-Encapsulate Transistors

### FEATURES

- High Current
- TRANSISTOR (NPN)

### MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



### MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	180	V
Collector-Emitter Voltage	$V_{CEO}$	120	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	1.5	A
Collector Power Dissipation	$P_C$	1.25	W
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	100	°C/W
Junction Temperature	$T_j$	150	°C
Storage Temperature	$T_{stg}$	-55~+150	°C

### ELECTRICAL CHARACTERISTICS $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1\text{mA}, I_E = 0$	180			V
Collector-emitter sustaining voltage	$V_{CEO(SUS)}$	$I_C = 0.03\text{A}, I_B = 0$	120			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1\text{mA}, I_C = 0$	5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = 30\text{V}, I_E = 0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$			10	$\mu\text{A}$
DC current gain	$h_{FE(1)}$	$V_{CE} = 2\text{V}, I_C = 150\text{mA}$	100		200	
	$h_{FE(2)}$	$V_{CE} = 2\text{V}, I_C = 5\text{mA}$	25			
	$h_{FE(3)}$	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$				
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$			0.5	
Base-emitter voltage	$V_{BE}$	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$			11	V

\* Pulse test: pulse width  $\leq 350\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .

RATINGS AND CHARACTERISTIC CURVES

